

ABSTRACT

WAFER PRODUCING METHOD

Disclosed herein is a wafer producing method for producing an SiC wafer from an SiC ingot. The wafer producing method includes a first modified layer forming step and a second modified layer forming step. In the first modified layer forming step, a first laser beam having a first power is applied to the ingot to thereby discretely form a plurality of first modified layers at a first depth inside the ingot. In the second modified layer forming step, a second laser beam having a second power greater than the first power is applied to the ingot in the condition where the focal point of the second laser beam is set at a depth greater than the first depth and a beam spot of the second laser beam overlaps any one of the plural first modified layers, thereby continuously forming a plurality of second modified layers connected in a line at the first depth. Further, cracks are also formed on both sides of the line of the plural second modified layers so as to extend along a c-plane in the ingot.

(Figure 6B)